

Multi-scale modeling of H interactions on W surfaces and W/Cu interlayers

Y. Silva-Solís¹, J. D. Cremé¹, J. Denis¹, E. A. Hodille² and Y. Ferro¹

¹Aix-Marseille University, CNRS, PIIM, F-13013 Marseille, France ²CEA, IRFM, F-13108 Saint-Paul-lez-Durance, France



- 2. Methodology.
- 3. Surface, sub-surface and bulk phenomenon.
- 4. Interface: W/Cu in the PFUs.
- 5. Conclusions.

What are we interested in?



Plasma-material interaction

Strong interaction with the plasma

Effect of H atoms

What are we interested in?



- 2. Methodology.
- 3. Surface, sub-surface and bulk phenomenon.
- 4. Interface: W/Cu in the PFUs.
- 5. Conclusions.

- 2.1. Electronic structure calculations (DFT).
 - 2.2. From DFT to macroscale properties with Statistical Thermodynamics.
 - 2.3. From DFT to kinetic modeling.
- 3. Surface, sub-surface and bulk phenomenon.
- 4. Interface: W/Cu in the PFUs.
- 5. Conclusions.

2.1. Methodology – Electronic structure by DFT



Macroscopic component





- 2.1. Electronic structure calculations (DFT).
 - 2.2. From DFT to macroscale properties with Statistical Thermodynamics.
 - 2.3. From DFT to kinetic modeling.
- 3. Surface, sub-surface and bulk phenomenon.
- 4. Interface: W/Cu in the PFUs.
- 5. Conclusions.

- 2.1. Electronic structure calculations (DFT).
- 2.2. From DFT to macroscale properties with Statistical Thermodynamics.
 - 2.3. From DFT to kinetic modeling.
- 3. Surface, sub-surface and bulk phenomenon.
- 4. Interface: W/Cu in the PFUs.
- 5. Conclusions.

H in W bulk by DFT calculations



H in W bulk by DFT calculations

Statistical thermodynamics

Gibbs free energy of the system based on DFT





H in W bulk by DFT calculations



Statistical thermodynamics

Gibbs free energy of the system based on DFT

$$H_{2} \text{ gas}$$

$$g_{H_{2}} = g_{H_{2}}^{\circ} + k_{B}T \ln\left(\frac{P}{P^{\circ}}\right)$$

$$g_{H_{2}}^{\circ} = \left(e_{H_{2}}^{DFT} + e_{H_{2}}^{vib} + e_{H_{2}}^{rot} + e_{H_{2}}^{trans} + P\Delta V\right) - T\left(s_{H_{2}}^{vib} + s_{H_{2}}^{rot} + s_{H_{2}}^{\circ}\right)$$

Macroscopic system

Any sub-system *j*

$$g_{j} = e_{j} - Ts_{j}$$
Potential to be minimized
$$G = \frac{1}{2} \left(N_{\rm H} - n_{int} - \sum_{j=0}^{12} j n_{j} \right) \mu_{\rm H_{2}} + n_{int} g_{int} + \left(\sum_{j=0}^{12} j n_{j} g_{j} \right) - TS_{conf}$$

AMPMI 2024 | 14



Solubility of H in W without defects



H reservoir was treated as real and ideal gas [1]

[1] E. A. Hodille, Physical Review Materials, 2 (2018) 093802... [2] R. Frauenfelder, J. Vac. Sci Technol 6 (1969).

Exp B-

-- Exp B+

3

- 2.1. Electronic structure calculations (DFT).
- 2.2. From DFT to macroscale properties with Statistical Thermodynamics.
 - 2.3. From DFT to kinetic modeling.
- 3. Surface, sub-surface and bulk phenomenon.
- 4. Interface: W/Cu in the PFUs.
- 5. Conclusions.

- 2.1. Electronic structure calculations (DFT).
- 2.2. From DFT to macroscale properties with Statistical Thermodynamics.
- 2.3. From DFT to kinetic modeling.
- 3. Surface, sub-surface and bulk phenomenon.
- 4. Interface: W/Cu in the PFUs.
- 5. Conclusions.

Diffusion of H atoms in perfect W bulk





Interstitial H_i

Diffusion coefficient

$$D(T) \approx D_o \exp\left[-\frac{E_{diff}}{k_B T}\right]$$



N. Fernandez, et al., Acta Materialia 94 (2015), 307-318.

[2] R. Frauenfelder, J. Vac. Sci Technol 6 (1969).
[3] A. P. Zakharov et.al., SSR 9 (1975), 149–153.
[4] G. Benamati, et.al., J. of Nucl. Matter. 283 (2000), 1033–1037.

Diffusion of H atoms in perfect W bulk





Interstitial H_i

Diffusion coefficient

$$D(T) \approx D_o \exp\left[-\frac{E_{diff}}{k_B T}\right]$$



N. Fernandez, et al., Acta Materialia 94 (2015), 307-318.

[2] R. Frauenfelder, J. Vac. Sci Technol 6 (1969).
[3] A. P. Zakharov et.al., SSR 9 (1975), 149–153.
[4] G. Benamati, et.al., J. of Nucl. Matter. 283 (2000), 1033–1037.

Diffusion and trapping in complex environments



N. Fernandez, et al., Acta Materialia 94 (2015), 307-318.

20

- 2.1. Electronic structure calculations (DFT).
- 2.2. From DFT to macroscale properties with Statistical Thermodynamics.
- 2.3. From DFT to kinetic modeling.
- 3. Surface, sub-surface and bulk phenomenon.
- 4. Interface: W/Cu in the PFUs.
- 5. Conclusions.

- 1. Introduction.
- 2. Methodology.
- 3. Surface, sub-surface and bulk phenomenon.
- 4. Interface: W/Cu in the PFUs.
- 5. Conclusions.

3. Surface, sub-surface and bulk phenomenon



3. Surface, sub-surface and bulk phenomenon



3. Surface, sub-surface and bulk phenomenon



Interface: W/Cu in the PFUs



AMPMI 2024 | 26

- 1. Introduction.
- 2. Methodology.
- 3. Surface, sub-surface and bulk phenomenon.
- 4. Interface: W/Cu in the PFUs.
- 5. Conclusions.

- 1. Introduction.
- 2. Methodology.
- 3. Surface, sub-surface and bulk phenomenon.

4. Interface: W/Cu in the PFUs.

- 4.1. Atomic scale model of the W/Cu interface.
 - 4.2. H solubility at the W/Cu interface.
 - 4.3. H diffusivity at the W/Cu interface.
 - 4.4. Propagation of defects towards the W/Cu interface.
- 5. Conclusions.

How to match the W and Cu bulks?

- 1. Different cell parameters and Bravais lattice.
- 2. Different crystallographic orientations can be considered.



W body centered cubic (bcc) a = 3.187 Å **Cu** face centered cubic (fcc) a = 3.620 Å

How to match the W and Cu bulks?

- 1. Different cell parameters and Bravais lattice.
- 2. Different crystallographic orientations can be considered.



W body centered cubic (bcc) a = 3.187 Å **Cu** face centered cubic (fcc) a = 3.620 Å

W(001)/Cu(001)R45°

High energy of separation.

W(001) is known to reconstruct.

W(001)/Cu(001)R45°





How to match the W and Cu bulks?

- 1. Different cell parameters and Bravais lattice.
- 2. Different crystallographic orientations can be considered.



W body centered cubic (bcc) a = 3.187 Å **Cu** face centered cubic (fcc) a = 3.620 Å

W(001)/Cu(001)R45°

High energy of separation.

W(001) is known to reconstruct.

<section-header>





How to match the W and Cu bulks?

- 1. Different cell parameters and Bravais lattice.
- 2. Different crystallographic orientations can be considered.



W body centered cubic (bcc) a = 3.187 Å **Cu** face centered cubic (fcc) a = 3.620 Å

W(001)/Cu(001)R45°

High energy of separation. W(001) is known to reconstruct.



Most compact layers. Lower energy of the interface. W(001)/Cu(001)R45°



W(110)/Cu(111)

















Relaxed structure

[6] Y. Silva-Solís et. al., Nuclear Materials & Energy 37 (2023) 101516.
[7] H. Wormeester et. al., Surf. Sci. 377 (1997) 988–991.
[8] T.R.J. Bollmann et. al., Phys. Rev. B 85 (2012) 125417.







[6] Y. Silva-Solís et. al., Nuclear Materials & Energy 37 (2023) 101516. [7] H. Wormeester et. al., Surf. Sci. 377 (1997) 988–991. [8] T.R.J. Bollmann et. al., Phys. Rev. B 85 (2012) 125417.



[6] Y. Silva-Solís et. al., Nuclear Materials & Energy 37 (2023) 101516.
[7] H. Wormeester et. al., Surf. Sci. 377 (1997) 988–991.
[8] T.R.J. Bollmann et. al., Phys. Rev. B 85 (2012) 125417.
4.1. Atomic scale model of the W/Cu interface





4.1. Atomic scale model of the W/Cu interface



At both the W(001)/Cu(001) and W(110)/Cu(111) interfaces

Copper reconstructs in a hexagonal compact structure

Common feature to both interface despite they are different models

- 1. Introduction.
- 2. Methodology.
- 3. Surface, sub-surface and bulk phenomenon.

- 4.1. Atomic scale model of the W/Cu interface.
 - 4.2. H solubility at the W/Cu interface.
 - 4.3. H diffusivity at the W/Cu interface.
 - 4.4. Propagation of defects towards the W/Cu interface.
- 5. Conclusions.

- 1. Introduction.
- 2. Methodology.
- 3. Surface, sub-surface and bulk phenomenon.

- 4.1. Atomic scale model of the W/Cu interface.
- 4.2. H solubility at the W/Cu interface.
 - 4.3. H diffusivity at the W/Cu interface.
 - 4.4. Propagation of defects towards the W/Cu interface.
- 5. Conclusions.







Solubility is higher in the **Cu** than in **W**

Solution energy is lowest at the **interface**





Solubility is higher in the Cu than in W

Solution energy is lowest at the **interface**

Hydrogen solubility is high at the interface





Solubility is higher in the Cu than in W

Solution energy is lowest at the **interface**

Hydrogen solubility is high at the interface

How to consider the effect of temperature?



Solubility of H at the W/Cu interface and in the W and Cu bulks





Tungsten

The hydrogen solubility is lower in the vicinity of the interface.

Solubility of H at the W/Cu interface and in the W and Cu bulks





Tungsten

The hydrogen solubility is lower in the vicinity of the interface.

Interface

The hydrogen solubility is similar to that in perfect **Cu**. The hydrogen solubility is higher at the plane of the interface.

Solubility of H at the W/Cu interface and in the W and Cu bulks





Tungsten

The hydrogen solubility is lower in the vicinity of the interface.

Interface

The hydrogen solubility is similar to that in perfect **Cu**. The hydrogen solubility is higher at the plane of the interface.

Hydrogen might segregate at the interface

Solubility of H at the W/Cu interface and in the W and Cu bulks





Tungsten

The hydrogen solubility is lower in the vicinity of the interface.

Interface

The hydrogen solubility is similar to that in perfect **Cu**. The hydrogen solubility is higher at the plane of the interface.

Hydrogen might segregate at the interface

What about diffusion?

- 1. Introduction.
- 2. Methodology.
- 3. Surface, sub-surface and bulk phenomenon.

- 4.1. Atomic scale model of the W/Cu interface.
- 4.2. H solubility at the W/Cu interface.
 - 4.3. H diffusivity at the W/Cu interface.
 - 4.4. Propagation of defects towards the W/Cu interface.
- 5. Conclusions.

- 1. Introduction.
- 2. Methodology.
- 3. Surface, sub-surface and bulk phenomenon.

- 4.1. Atomic scale model of the W/Cu interface.
- 4.2. H solubility at the W/Cu interface.
- 4.3. H diffusivity at the W/Cu interface.
 - 4.4. Propagation of defects towards the W/Cu interface.
- 5. Conclusions.

4.3. H diffusivity within the W/Cu interface

Minimum energy path for H across the W/Cu interface



- 2 paths across the **interface**
- 1 path in the plane of the **interface**









- 1. Introduction.
- 2. Methodology.
- 3. Surface, sub-surface and bulk phenomenon.

- 4.1. Atomic scale model of the W/Cu interface.
- 4.2. H solubility at the W/Cu interface.
- 4.3. H diffusivity at the W/Cu interface.
 - 4.4. Propagation of defects towards the W/Cu interface.
- 5. Conclusions.

- 1. Introduction.
- 2. Methodology.
- 3. Surface, sub-surface and bulk phenomenon.

- 4.1. Atomic scale model of the W/Cu interface.
- 4.2. H solubility at the W/Cu interface.
- 4.3. H diffusivity at the W/Cu interface.
- 4.4. Propagation of defects towards the W/Cu interface.
- 5. Conclusions.

4.4. Porpagation of defects towards the W/Cu interface

Does the **hcp** reconstruction propagate into the **Cu** bulk? $W(100)/Cu^{hcp}(11\bar{2}0)$ $\mathrm{Cu}^{\mathrm{fcc}}$

MD simulations only in Cu bulk vc-relax -----> NPT ----> NV



Does the **hcp** reconstruction propagate into the **Cu** bulk?



 $W(100)/Cu^{hcp}(11\bar{2}0)$ Cu^{fcc}

MD simulations only in Cu bulk

- Cu^{fcc} structure propagates into the Cu^{hcp} due to the recrystallization of the bulk.
- Point and extended defects propagate towards the W/Cu interface.





Summary of the W/Cu interface

- Hydrogen solubility is high at the plane of the interface.
- **Diffusivity of hydrogen** is **lower** at the plane of the **interface**.
- **Point and extended defects** are **propagated towards** the **interface**.



Summary of the W/Cu interface

- Hydrogen solubility is high at the plane of the interface.
- **Diffusivity of hydrogen** is **lower** at the plane of the **interface**.
- **Point and extended defects** are **propagated towards** the **interface**.

Segregation of H within the W/Cu interface



Summary of the W/Cu interface

- Hydrogen solubility is high at the plane of the interface.
- **Diffusivity of hydrogen** is **lower** at the plane of the **interface**.
- **Point and extended defects** are **propagated towards** the **interface**.

Segregation of H within the W/Cu interface

The W/Cu interface behaves as a sink for H atoms

- 1. Introduction.
- 2. Methodology.
- 3. Surface, sub-surface and bulk phenomenon.

- 4.1. Atomic scale model of the W/Cu interface.
- 4.2. H solubility at the W/Cu interface.
- 4.3. H diffusivity at the W/Cu interface.
- 4.4. Propagation of defects towards the W/Cu interface.
- 5. Conclusions.

- 1. Introduction.
- 2. Methodology.
- 3. Surface, sub-surface and bulk phenomenon.
- 4. Interface: W/Cu in the PFUs.
- 5. Conclusions.



Material modeling starting from the atomic scale - Multiscale approach

Equilibrium properties (Thermo model)

Dynamic properties (Kinetic model)

From the W surface to the W/Cu interface and beyond.

H segregation at the W/Cu interface

Future perspectives





Our team only ceam





Multi-scale modeling of H interactions on W surfaces and W/Cu interlayers

Y. Silva-Solís¹, J. D. Cremé¹, J. Denis¹, E. A. Hodille² and Y. Ferro¹

¹Aix-Marseille University, CNRS, PIIM, F-13013 Marseille, France ²CEA, IRFM, F-13108 Saint-Paul-lez-Durance, France



Backup slides

Y. Silva-Solís¹, J. D. Cremé¹, J. Denis¹, E. A. Hodille² and Y. Ferro¹

¹Aix-Marseille University, CNRS, PIIM, F-13013 Marseille, France ²CEA, IRFM, F-13108 Saint-Paul-lez-Durance, France



Thermodynamics vs Kinetic at steady-state





Thermodynamics vs Kinetic at steady-state

1.75 c)

1.50



Thermodynamics vs Kinetic at steady-state


Thermodynamics vs Kinetic at steady-state



4.3. H diffusivity within the W/Cu interface

Simplifying the kinetic model



$$\nu_s = 7.84 \times 10^{12} \exp\left(-\frac{1.01}{k_B T}\right)$$

 τ_s is determined from T = 340K to 1000K

Simplifying the kinetic model



$$\nu_s = 7.84 \times 10^{12} \exp\left(-\frac{1.01}{k_B T}\right)$$

 τ_s is determined from T = 340K to 1000K

An Arrhenius fit is obtained.

The complex energy profile behaves like a single step diffusion mechanism.

Kinetic model simplifies to a fictitious model with:

- Single diffusion step.
- $E_a = 1.01 \text{ eV}$
- $v_0 = 7.84 \times 10^{12} \text{ Hz}$

Simplifying the kinetic model



$$\nu_s = 7.84 \times 10^{12} \exp\left(-\frac{1.01}{k_B T}\right)$$

 τ_s is determined from T = 340K to 1000K

An Arrhenius fit is obtained.

The complex energy profile behaves like a single step diffusion mechanism.

Kinetic model simplifies to a fictitious model with:

- Single diffusion step.
- $E_a = 1.01 \text{ eV}$
- $v_0 = 7.84 \times 10^{12} \text{ Hz}$

Diffusivity of H

Plane W/Cu < Cu < W

The interface behaves as a sink